

Description

This invention relates to a method of fabricating a magnetic recording disk and in particular to a method of fabricating a disk having a thin film metal alloy magnetic layer and a protective overcoat of a hydrogen-carbon film.

Thin film metal alloy magnetic recording disks typically comprise a substrate, such as an aluminum-magnesium (AlMg) alloy with a nickel-phosphorous (NiP) surface coating, a cobalt-based alloy sputter deposited as the magnetic layer on the substrate, and a protective overcoat, such as a sputter-deposited amorphous carbon film, formed on the magnetic layer. Such disks may also include a sputter-deposited underlayer, such as a layer of chromium (Cr), chromium-vanadium (CrV) or tungsten (W), between the substrate and the magnetic layer, and a sputter-deposited adhesion layer, such as a Cr, W or titanium (Ti) layer, between the magnetic layer and the protective overcoat. A general description of the structure of such thin film disks is given in U.S. patents 4,610,911 to Opfer et al., and 4,552,820 to Lin et al.

One of the problems with such disks is the suitability of the protective overcoat to provide corrosion resistance for the underlying magnetic layer and resistance to wear caused by contact of the disk by the air-bearing slider which carries the magnetic recording head. Protective overcoats of amorphous carbon formed by the sputtering of a graphite target in the presence of pure argon (Ar), such as described in U.S. patent 4,502,125 to Nelson et al., have not been proven to provide the magnetic layer with satisfactory corrosion resistance.

Amorphous hydrogenated carbon films formed by chemical vapor deposition (CVD) plasma decomposition of hydrocarbon gases or reactive sputtering of a graphite target in an atmosphere of argon and hydrocarbon gases have been suggested as suitable for use as thin film disk protective overcoats. Japanese published but not examined patent application (Kokai) 60-155668 describes a protective overcoat formed by sputtering carbon in an atmosphere of various hydrocarbon gases, and Japanese Kokai 60-157725 describes a protective overcoat formed by sputtering a carbon target in the presence of various hydrocarbon gases or a mixture of such hydrocarbon gases with Ar, helium (He) or hydrogen (H₂).

The invention is claimed in the attached claim 1. It is a method of fabricating a thin film disk by sputter depositing both the magnetic layer and protective overcoat in an atmosphere consisting essentially of Ar and H₂. The method may also include the steps of forming an underlayer for the magnetic layer and an adhesion layer for the protective overcoat in the same Ar-H₂ atmosphere. Because the entire disk structure can be formed by sputter deposition in the same atmosphere, the method permits continuous in-line fabrication of the disks. The method results in a disk with excellent magnetic properties and with a hydrogenated carbon (C:H) protective overcoat formed by the reaction of the H₂ gas with the carbon from the sputtering target. The resulting overcoat has corrosion resistance and wear resistance exceeding that of conventional amorphous carbon overcoats.

For a fuller understanding of the nature and advantages of the present invention reference should be made to the following detailed description taken in conjunction with the accompanying drawings, wherein

fig. 1 is a plot of coercivity (H_c) and coercivity squareness (S*) as a function of %H₂ in the Ar-H₂ atmosphere during the fabrication of the complete disk structure, including the magnetic layer and the hydrogenated carbon overcoat; and

fig. 2 is a comparison of corrosion current as a function of pH for a conventional amorphous carbon overcoat and for a hydrogenated carbon overcoat formed by the process of the present invention.

In order to study the feasibility of fabricating a thin film disk with a hydrogenated carbon overcoat formed by the known technique of reactive sputter deposition in a hydrocarbon atmosphere, the film structures of various disks were formed by sputter deposition in argon-methane (Ar-CH₄) atmospheres with varying amounts of CH₄. The magnetic properties of such disks were then examined. The disks were formed in a single pump down of a RF powered S-Gun (registered trademark of Varian Associates) magnetron sputtering chamber containing a silicon (Si) substrate and targets of Cr₈₀V and cobalt-platinum-chromium (Co₇₇PtCr). Ar and CH₄ were introduced into the chamber and maintained at a pressure of approximately 3-4 m Torr (0.4-0.53 Pa). The Cr₈₀V target was activated at 320 watts with a -50 V. bias on the substrate, resulting in a 300 Angstrom thick underlayer formed on the Si substrate at a rate of approximately 33 Angstrom/minute. Thereafter, the Co₇₇PtCr target was activated at 270 watts with the substrate maintained at ground potential, resulting in a 300 Angstrom (30 nm) thick Co₇₇PtCr magnetic layer formed on the Cr₈₀V underlayer.

As shown in Table 1, the presence of CH₄ in the atmosphere during the sputter deposition of the cobalt-based alloy magnetic layer substantially reduced the coercivity (H_c) and rendered the disks unacceptable as a magnetic recording medium.

$\%CH_4$ in Ar- CH_4	0	20	50
H_c (Oersteds)	1620	210	190

Disk Structure: Si/300 Å Cr₈₀ V/300 Å Co₇₇PtCr
(1 Oersted = 80 A/m)

Thus, the results of Table 1 indicate that, regardless of the suitability of an overcoat formed by reactive sputtering of a carbon target in an Ar- CH_4 atmosphere, such an overcoat would have to be formed as a separate step in the fabrication process, either by removing the disks from one sputtering chamber with an Ar atmosphere and placing them in a second chamber with an Ar- CH_4 atmosphere, or by introducing CH_4 into the sputtering chamber after the Co-based magnetic layer has been completely formed. Neither procedure is compatible with a continuous in-line disk fabrication process, wherein the disk substrates continuously enter and exit a single sputtering station.

Disks having a film structure similar to those whose test results are listed in Table 1 were fabricated under similar sputtering conditions, with the exception that the atmosphere was Ar- H_2 , with varying amounts of H_2 . In addition, a hydrogenated carbon overcoat of 250 Angstrom (25 nm) thickness was also formed on the CoPtCr magnetic layer of such disks following the deposition of the magnetic layer. In the fabrication of such disks, a Cr₈₀V underlayer was first formed on the substrate in the S-Gun chamber with the Ar- H_2 atmosphere maintained at 3-4 m Torr (0.4-0.53 Pa), RF power to the Cr₈₀V target of 235 watts, and a -50V. bias on the substrate. This resulted in a 400 Angstrom (40 nm) thick underlayer deposited at a rate of approximately 32 Angstroms/minute (3.2 nm/minute). A Co₇₅PtCr magnetic film was then formed in the same atmosphere by activating the Co₇₅PtCr target at 240 watts, with the substrate maintained at ground potential. A 350 Angstrom (35 nm) thick Co₇₅PtCr magnetic film was formed at a deposition rate of approximately 37 Angstroms (3.7 nm)/minute. A 200 Angstrom (20 nm) thick hydrogenated carbon overcoat was then formed on the magnetic film at a rate of approximately 6-7 Angstroms (0.6-0.7 nm)/minute by activating a graphite target at 250 watts while maintaining the substrate at ground potential. These disk structures were formed on both Si and AlMg-NiP substrates.

The H_c and coercivity squareness (S') of such disks were measured and are shown as a function of percentage H_2 in Fig. 1. As is apparent from Fig. 1, the sputter deposition of the Cr₈₀V underlayers and Co₇₅PtCr magnetic layers in the reactive Ar- H_2 environment unexpectedly had no effect on the magnetic properties of the disks. The complete lack of any degradation in magnetic properties was also observed when the composition of the magnetic layer was changed to Co₆₈PtCr.

The results shown in Fig. 1 clearly indicate that it is possible to fabricate thin film metal alloy disks with a hydrogenated carbon overcoat by a continuous in-line process wherein all layers in the disk structure are sputter deposited in an atmosphere consisting essentially of Ar and H_2 .

The corrosion resistance of the hydrogenated carbon overcoat formed by sputtering in Ar- H_2 is substantially improved over the conventional amorphous carbon formed by sputtering in pure Ar. Fig. 2 illustrates the measured corrosion current in an electrolyte (0.1 normal Na_2SO_4) for disks with a CoPtCr magnetic layer at various pH levels of the electrolyte for the two types of overcoats.

The hydrogenated carbon overcoat formed in the Ar- H_2 sputtering atmosphere at relatively low (8%) H_2 concentration also exhibits corrosion resistance comparable to that of hydrogenated carbon overcoats formed in Ar- CH_4 sputtering atmospheres with relatively high (50%) CH_4 concentrations, as determined by measured corrosion currents.

The preferred minimum amount of H_2 necessary during the process is believed to be approximately 1%. At H_2 amounts less than approximately 1% in the Ar- H_2 atmosphere, there was no significant improvement in corrosion resistance in such overcoats over conventional amorphous carbon overcoats.

A CoPtCr disk made according to the process of this invention (4% H_2) with a 100 Angstrom (10 nm) thick Ti adhesion layer, a 200 Angstrom thick C:H overcoat and a conventional perfluoroalkyl polyether type

lubricant applied to the C:H overcoat exhibited excellent wear resistance and reduction in static friction when tested for over 10,000 start-stop cycles of a disk file, during which the slider contacts the same track region of the disk. No wear tracks were observed and the static friction between the slider and the disk substantially decreased as the number of start-stop cycles increased.

5 The structures of hydrogenated carbon films formed according to the above described process were analyzed by Raman spectrometry. The peak intensity occurred at 1500-1550 wavenumbers (cm^{-1}). The peak intensity for a film formed in Ar-H₂ (12% H₂) is significantly less than for a film formed in Ar-H₂ (8% H₂). The lower peak intensity indicates more sp³ bonding in the film, since the Raman efficiency for sp³ bonds is less than for sp² bonds.

10 In a preferred embodiment for use of the above described process in the fabrication of thin film metal alloy magnetic recording disks, all of the films in the completed disk structure are sputter deposited in a production type in-line sputtering system having a single sputtering station. For example, if the disk structure is to include an underlayer beneath the magnetic layer and an adhesion layer between the hydrogenated carbon overcoat, then there would be four target areas within the single station. Ar and H₂ are introduced into the sputtering chamber. All of the target areas are exposed to the same Ar-H₂ atmosphere which is maintained at the same pressure during the entire process. The disk substrates enter the station on a continuous transport system and pass the target areas in succession. If an underlayer is to be used, then the substrates pass in front of that specific sputtering target for a predetermined time sufficient to form the desired underlayer thickness on the substrate. The disks then pass the targets for the magnetic layer and the adhesion layer. Finally the disks pass the graphite target to form the hydrogenated carbon overcoat. In this manner the entire disk structure is fabricated in a continuous in-line process which has H₂ present in the sputtering atmosphere. The H₂, which is necessary to form the hydrogenated carbon overcoat, has no adverse effect on the formation of any of the other films in the disk structure and no adverse effect on the magnetic properties of the completed disk.

25 The disk structures formed by the process of this invention included a CrV underlayer and a CoPtCr magnetic layer. However; the process is fully applicable to disk structures without an underlayer and with other Co-based magnetic layer compositions.

Claims

- 30 1. A method of fabricating a thin film magnetic recording disk comprising the steps of:
forming a magnetic layer on a disk substrate by sputter depositing, in an atmosphere consisting essentially of argon and hydrogen, a film of a cobalt-based alloy; and
sputter depositing over the magnetic layer, in substantially the same atmosphere, a hydrogen-carbon film from a carbon target.
- 35 2. The method according to claim 1 further comprising the step of, prior to forming the magnetic layer, sputter depositing an underlayer on the substrate in an atmosphere consisting essentially of argon and hydrogen.
- 40 3. The method according to claim 1 further comprising the step of, prior to sputter depositing the hydrogen-carbon film, sputter depositing an adhesion layer on the magnetic layer in substantially the same atmosphere.
- 45 4. A sputter deposition apparatus for fabricating a thin film magnetic recording disk comprising:
sputtering targets of a cobalt-based alloy and carbon in a single sputtering station;
means for exposing the targets to the same atmosphere consisting essentially of Ar and H₂, the H₂ being present in an amount greater than approximately 1% of the Ar-H₂; and
means for passing a disk substrate first past the cobalt-based alloy target and then past the carbon target in order to form a magnetic layer and a hydrogenated carbon overcoat, respectively.
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Patentansprüche

- 55 1. Verfahren zur Herstellung einer magnetischen Aufzeichnungsplatte mit einem dünnen Film, das die folgenden Schritte umfaßt:
Bildungen einer magnetischen Schicht auf einem Plattensubstrat mittels Aufspatterns einer Schicht aus einer Kobaltlegierung in einer, im wesentlichen aus Argon und Wasserstoff bestehenden Atmosphäre und



lubricant applied to the C:H overcoat exhibited excellent wear resistance and reduction in static friction when tested for over 10,000 start-stop cycles of a disk file, during which the slider contacts the same track region of the disk. No wear tracks were observed and the static friction between the slider and the disk substantially decreased as the number of start-stop cycles increased.

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sputter depositing over the magnetic layer, in substantially the same atmosphere, a hydrogen-carbon film from a carbon target.
- 35 2. The method according to claim 1 further comprising the step of, prior to forming the magnetic layer, sputter depositing an underlayer on the substrate in an atmosphere consisting essentially of argon and hydrogen.
3. The method according to claim 1 further comprising the step of, prior to sputter depositing the hydrogen-carbon film, sputter depositing an adhesion layer on the magnetic layer in substantially the same atmosphere.
- 45 4. A sputter deposition apparatus for fabricating a thin film magnetic recording disk comprising:
sputtering targets of a cobalt-based alloy and carbon in a single sputtering station;
means for exposing the targets to the same atmosphere consisting essentially of Ar and H₂, the H₂ being present in an amount greater than approximately 1% of the Ar-H₂; and
means for passing a disk substrate first past the cobalt-based alloy target and then past the carbon target in order to form a magnetic layer and a hydrogenated carbon overcoat, respectively.
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Patentansprüche

- 55 1. Verfahren zur Herstellung einer magnetischen Aufzeichnungsplatte mit einem dünnen Film, das die folgenden Schritte umfaßt:
Bildungen einer magnetischen Schicht auf einem Plattensubstrat mittels Aufspurnern einer Schicht aus einer Kobaltlegierung in einer, im wesentlichen aus Argon und Wasserstoff bestehenden Atmosphäre und



Aufputtern eines Wasserstoff-Kohlenstoff-Films von einem Kohlenstoff-Target über die magnetische Schicht in einer, im wesentlichen gleichen Atmosphäre.

2. Verfahren nach Anspruch 1, das ferner den Schritt aufweist, daß vor dem Ausbilden der magnetischen Schicht auf das Substrat eine Unterlage in einer im wesentlichen aus Argon und Wasserstoff bestehenden Atmosphäre aufgesputtert wird.
3. Verfahren nach Anspruch 1, das ferner den Schritt aufweist, daß vor dem Aufputtern des Wasserstoff-Kohlenstoff-Films eine Adhäsionsschicht auf die magnetische Schicht in einer im wesentlichen gleichen Atmosphäre aufgesputtert wird.
4. Aufputtereinrichtung zur Herstellung einer magnetischen Aufzeichnungsplatte mit einem dünnen Film, die folgendes aufweist: Sputter-Targets aus einer Kobalt-Legierung und aus Kohlenstoff in einer einzelnen Sputterstation,
Mittel, um die Targets der gleichen Atmosphäre auszusetzen, die im wesentlichen aus Ar und H₂ besteht, wobei H₂ in einer Menge vorhanden ist, die größer als ungefähr 1 % des Ar-H₂ und Mittel, um das Plattensubstrat zuerst am Kobalt-Legierungstarget und dann am Kohlenstofftarget vorbeizuführen, um eine magnetische Schicht beziehungsweise einen hydrierten Kohlenstoffüberzug zu bilden.

20 Revendications

1. Procédé de fabrication d'un disque d'enregistrement magnétique à film mince, comprenant les étapes de :
formation d'une couche magnétique sur un substrat de disque par dépôt par pulvérisation dans une atmosphère consistant essentiellement en argon et en hydrogène, d'un film d'un alliage à base de cobalt; et
dépôt par pulvérisation sur la couche magnétique dans pratiquement la même atmosphère, d'un film d'hydrogène-carbone provenant d'une cible de carbone.
2. Procédé suivant la revendication 1, comprenant de plus, avant la formation de la couche magnétique, l'étape de dépôt par pulvérisation d'une sous-couche sur le substrat dans une atmosphère consistant essentiellement en argon et hydrogène.
3. Procédé suivant la revendication 1, comprenant de plus, avant le dépôt par pulvérisation du film d'hydrogène-carbone, l'étape de dépôt par pulvérisation d'une couche d'adhérence sur la couche magnétique pratiquement dans la même atmosphère.
4. Appareil de dépôt par pulvérisation pour la fabrication d'un disque d'enregistrement magnétique à film mince, comprenant:
des cibles de pulvérisation d'un alliage à base de cobalt et de carbone dans une unique station de pulvérisation;
des moyens pour exposer les cibles à la même atmosphère consistant essentiellement en Ar et H₂, l'hydrogène étant présent en une quantité supérieure à environ 1% du Ar-H₂; et
des moyens pour faire passer le substrat du disque d'abord devant la cible d'alliage à base de cobalt et ensuite devant la cible de carbone pour former respectivement une couche magnétique et un revêtement de carbone hydrogéné.